- ROM

Masked Rom, PROM, EPROM, EEPROM, Flash memory

-RAM

SRAM, DRAM

ROM (read-only memory)

= Galisma sirasinda sadeze oknabilir.

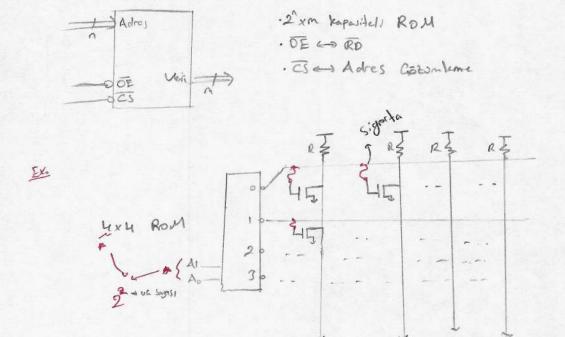
- * Non-Volatile: enerli kesildiginde veri kaybolmaz
- # 3086 reset vektorande Rom gerlesik

= Gesitler

- . Masked Rom: indatta programlanir
- *PROM (programmable ROM): Killanici 1 kere programlayabilir
- · EPROM (erasable prom): operasyon svrasnda kapali olan bir penceden uv Isikla silinebilia.
- · EE PROM (electrically Eprom): programlana valarindan silinnes: soglann
- · Flash Memory: bloklar halinde silme

*PROM: fuse Esigortal likk tek kullans.

ROM Blok Dijagrami



D3

100

* Sigortaların yahılıp Korunman, proglama Yapmamiti Sağlar.

- Sigorta yakılı => o

. N korunyor=1

014/2

- · Volatile
- . Hith ohuma, yatma
- . Main Memory

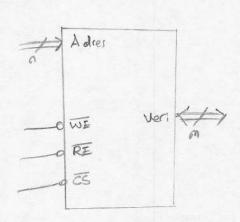
The opposite of random access.

Traversing memory is required

= GesiHers

- SRAM (static) FF lerle tosarlanming
- DRAM (dynamic) transitor we be pasition. [Bells aralihlarda degerber gincellenir]

SRAM



2 xm kapasitelo SRAM

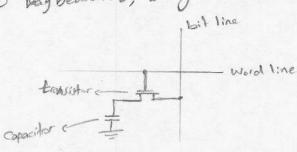
RE - RO

WE S WR

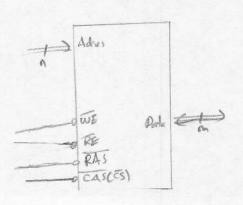
CS Co Adres Gozinlene

DRAM

- · kapasite + trans sitor aifflorinden dusor · futtige lotte deger belirli aralıklarla gencellenmek zorundadır
- . Her bir hocresi SRAMIa gare entegrade 4 kat daha az for kaplar
 - . O bay bedilmit, I goncellamorse kaybedilir.



(1-bil DRAM Cell)



2 xm kapasiteli ORAM

RE 40 RD

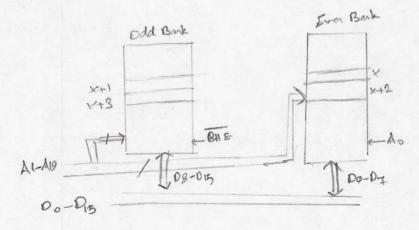
WE W WR

RAS : con select

CAS (CS) : column select

-lo un ile 2=14 hafita oft adreslatebilin

- Bir birim 8 bit.



" Tele adres 16-bit

Tek cycle'da olamaz tehadreiter 8-bit All'ea, Gift adrester 8-bit Al'ye ayrı ayrı cycle'larda aktorilir.

es separate bank decoder tele adresler ue cilt adresler icin ayrı ayrı as uclar kullanılır



Seperate Bank Strobe Tek CS. Lajik bir devre ile BHE ve Ap WE VE RE Igni

